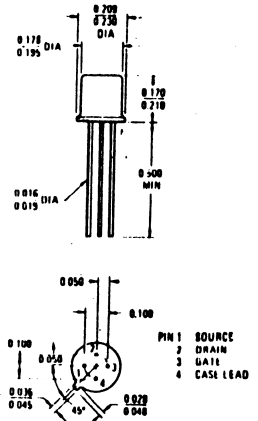


Silicon N-channel junction field-effect transistor designed for VHF/UHF amplifier applications.

(T0-72)



All JEDEC dimensions and notes apply

MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	30	Vdc
Drain-Gate Voltage	$V_{DG}$	30	Vdc
Gate-Source Voltage	$V_{GS}$	30	Vdc
Gate Current	$I_G$	10	mAdc
Total Device Dissipation @ $T_A @ 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 1.7	mW mW/ $^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-65 to +200	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Gate-Source Breakdown Voltage ( $I_G = -1.0 \mu\text{Adc}$ , $V_{DS} = 0$ )	$V_{(BR)GSS}$	30	-	Vdc
Gate-Source Cutoff Voltage ( $I_D = 1.0 \text{nAdc}$ , $V_{DS} = 15 \text{Vdc}$ )	$V_{GS(off)}$	-	6.0	Vdc
Gate-Source Voltage ( $I_D = 0.5 \text{mAdc}$ , $V_{DS} = 15 \text{Vdc}$ )	$V_{GS}$	1.0	5.5	Vdc
Gate-Source Forward Voltage ( $I_G = 1.0 \text{mAdc}$ , $V_{DS} = 0$ )	$V_{GS(f)}$	-	1.0	Vdc
Gate Reverse Current ( $V_{GS} = -20 \text{Vdc}$ , $V_{DS} = 0$ ) ( $V_{GS} = -20 \text{Vdc}$ , $V_{DS} = 0$ , $T_A = +150^\circ\text{C}$ )	$I_{GSS}$	-	100 200	$\mu\text{Adc}$

ON CHARACTERISTICS

Zero-Gate Voltage Drain Current* ( $V_{DS} = 15 \text{Vdc}$ , $V_{GS} = 0$ )	$I_{DSS}^*$	5.0	15	mAdc
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